PROCESS CPD05

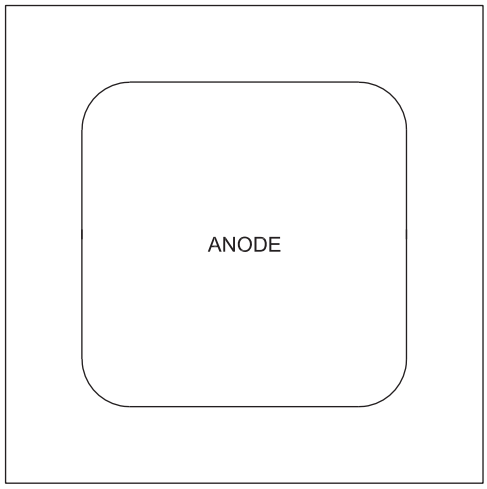
General Purpose Rectifier

1 Amp Glass Passivated Rectifier Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	51 x 51 MILS
Die Thickness	10.2 MILS
Anode Bonding Pad Area	36 x 36 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 4 INCH WAFER

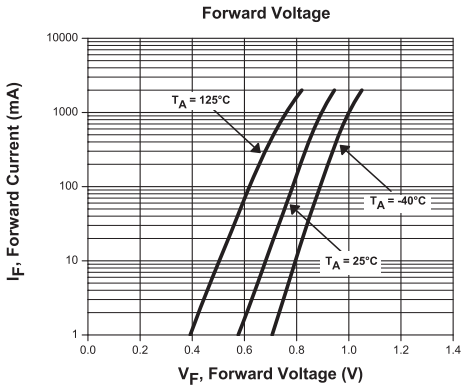
4,250

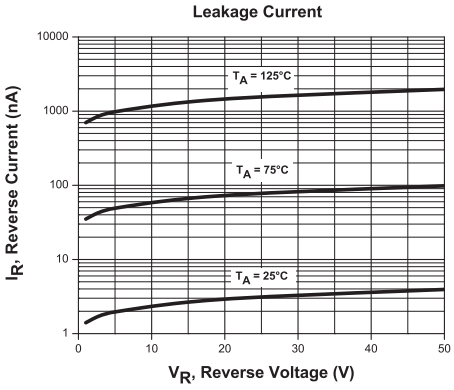
PRINCIPAL DEVICE TYPES

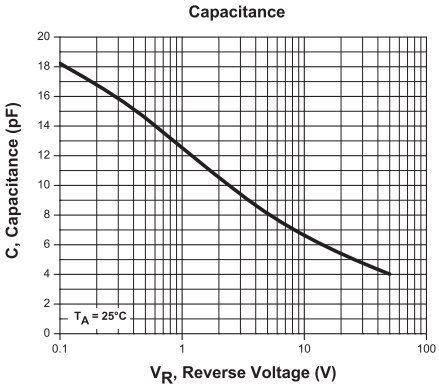
1N3611 thru 1N3614
1N4001 thru 1N4007
1N4245 thru 1N4249
1N5059 thru 1N5062
1N5391 thru 1N5399
1N5614 thru 1N5622
CMR1-02 Series
CMR1-02M Series

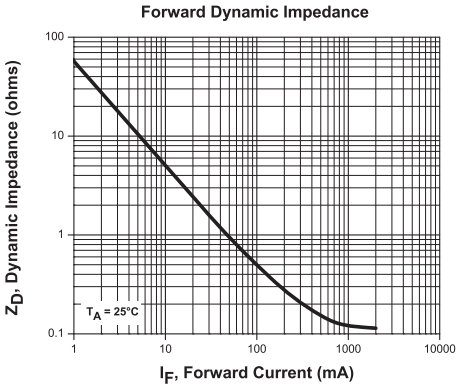
PROCESS CPD05

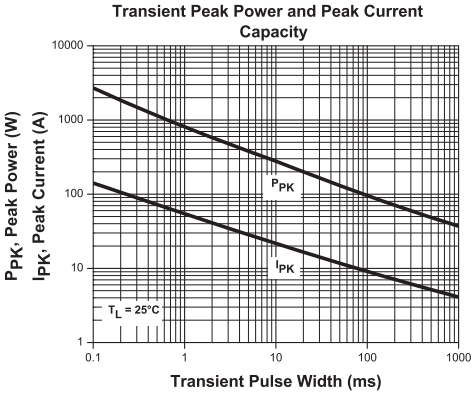
Typical Electrical Characteristics

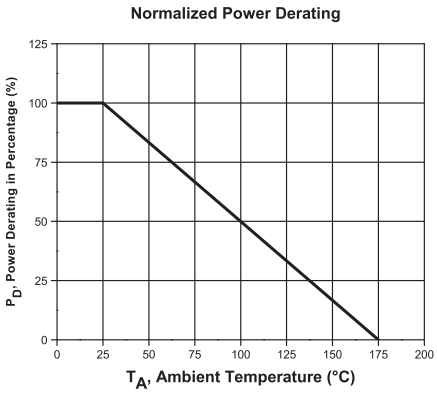












R4 (22-March 2010)